BRMUR1040CTBD

Rev.B .Mar.-2019

DATA SHEET

/ Descriptions

Ultrafast Recovery Diode in a TO-263 Plastic Package.

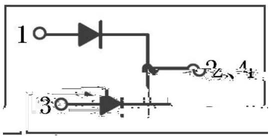
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode, PFC circuit.

/ Equivalent Circuit



/ Pinning H Q ñD •[

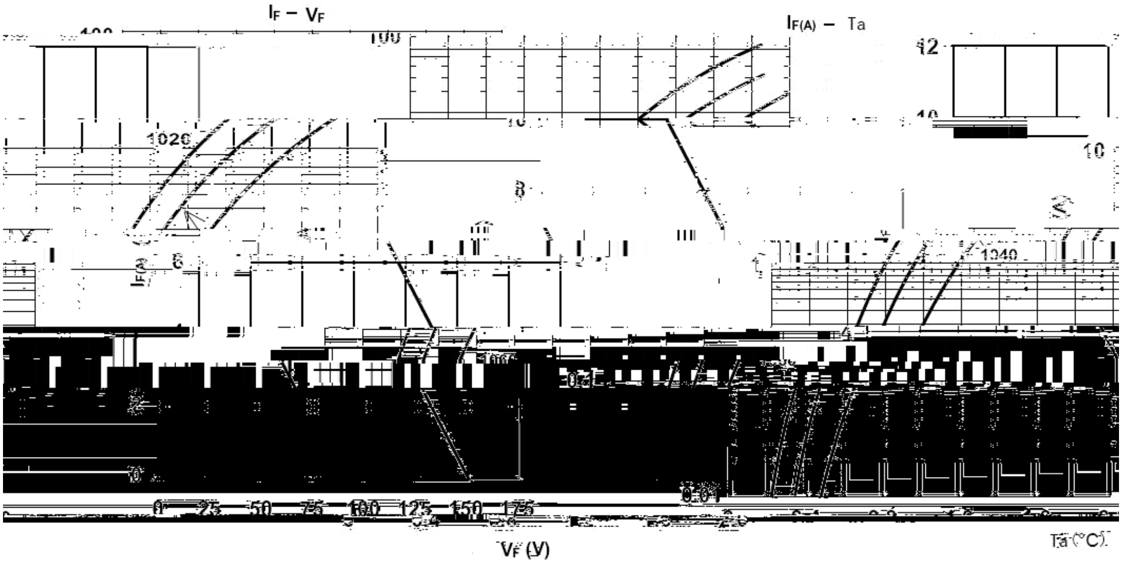
PIN1 Anode PIN 2 4 Cathode PIN 3 Anode

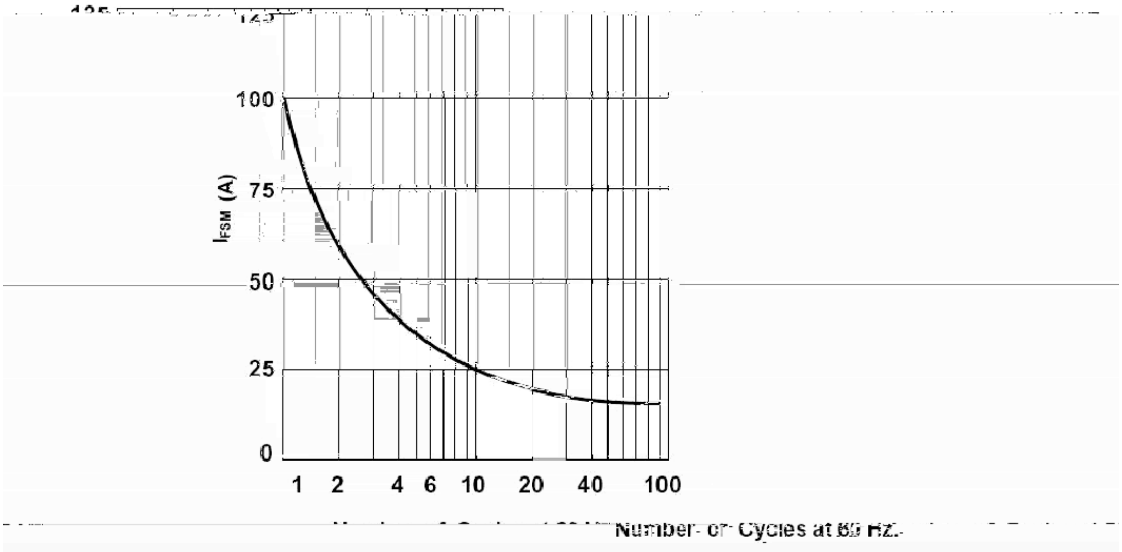
/ h_{FE} Classifications & Marking

See Marking Instructions.

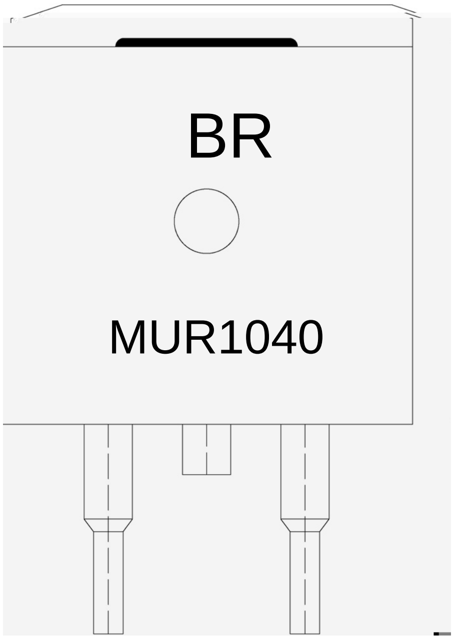
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	400	V
RMS Voltage	V_{RMS}	280	V
DC Blocking Voltage	V_{DC}	400	V
Peak Repetitive Forward Current	I_F	10	A
Non Repetitive Peak Surge Current	I_{FSM}	100	A
Maximum Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.8	/W
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristic Curve





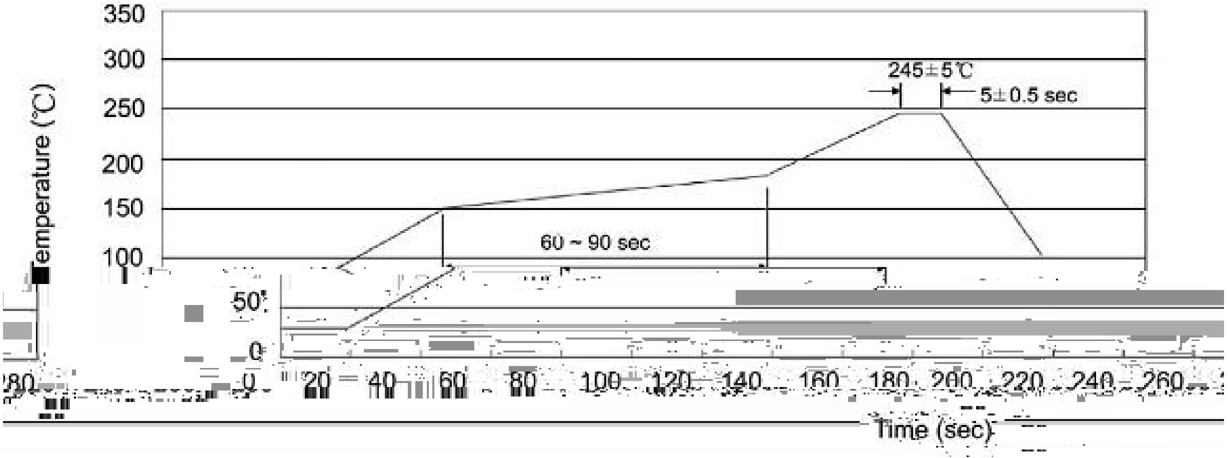
/ Marking Instructions



Note:

BR:	Company Code
MUR1040:	Product Type
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



	Note:
1 150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5